

DATA SHEET

BFG198

NPN 8 GHz wideband transistor

Product specification

1995 Sep 12



NPN 8 GHz wideband transistor

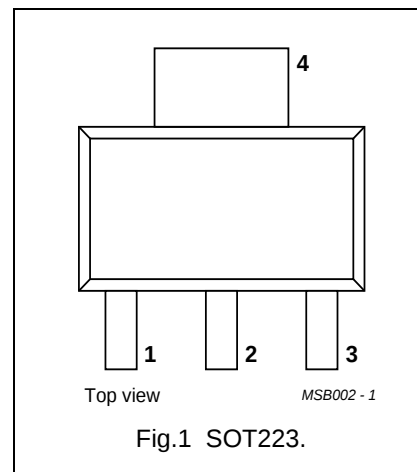
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DESCRIPTION

NPN planar epitaxial transistor in a plastic SOT223 envelope, intended for wideband amplifier applications. The device features a high gain and excellent output voltage capabilities.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	emitter
4	collector



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	—	—	20	V
V_{CEO}	collector-emitter voltage	open base	—	—	10	V
I_C	DC collector current		—	—	100	mA
P_{tot}	total power dissipation	up to $T_s = 135\text{ °C}$ (note 1)	—	—	1	W
h_{FE}	DC current gain	$I_C = 50\text{ mA}$; $V_{CE} = 5\text{ V}$; $T_j = 25\text{ °C}$	40	90	—	
f_T	transition frequency	$I_C = 50\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 1\text{ GHz}$; $T_{amb} = 25\text{ °C}$	—	8	—	GHz
G_{UM}	maximum unilateral power gain	$I_C = 50\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 500\text{ MHz}$; $T_{amb} = 25\text{ °C}$	—	18	—	dB
		$I_C = 50\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 800\text{ MHz}$; $T_{amb} = 25\text{ °C}$	—	15	—	dB
V_o	output voltage	$d_{im} = -60\text{ dB}$; $I_C = 70\text{ mA}$; $V_{CE} = 8\text{ V}$; $R_L = 75\text{ }\Omega$; $T_{amb} = 25\text{ °C}$; $f_{(p+q-r)} = 793.25\text{ MHz}$	—	700	—	mV

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	—	20	V
V_{CEO}	collector-emitter voltage	open base	—	10	V
V_{EBO}	emitter-base voltage	open collector	—	2.5	V
I_C	DC collector current		—	100	mA
P_{tot}	total power dissipation	up to $T_s = 135\text{ °C}$ (note 1)	—	1	W
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		—	175	°C

Note

- T_s is the temperature at the soldering point of the collector tab.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-s}$	thermal resistance from junction to soldering point	up to $T_s = 135\text{ °C}$ (note 1)	40	K/W

Note

- T_s is the temperature at the soldering point of the collector tab.

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = 5\text{ V}$	—	—	100	nA
h_{FE}	DC current gain	$I_C = 50\text{ mA}$; $V_{CE} = 5\text{ V}$	40	90	—	
C_c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = 8\text{ V}$; $f = 1\text{ MHz}$	—	1.5	—	pF
C_e	emitter capacitance	$I_C = i_c = 0$; $V_{EB} = 0.5\text{ V}$; $f = 1\text{ MHz}$	—	4	—	pF
C_{re}	feedback capacitance	$I_C = 0$; $V_{CE} = 8\text{ V}$; $f = 1\text{ MHz}$	—	0.8	—	pF
f_T	transition frequency	$I_C = 50\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 1\text{ GHz}$; $T_{amb} = 25\text{ °C}$	—	8	—	GHz
G_{UM}	maximum unilateral power gain; note 1	$I_C = 50\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 500\text{ MHz}$; $T_{amb} = 25\text{ °C}$	—	18	—	dB
		$I_C = 50\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 800\text{ MHz}$; $T_{amb} = 25\text{ °C}$	—	15	—	dB
V_o	output voltage	note 2	—	750	—	mV
		note 3	—	700	—	mV
d_2	second order intermodulation distortion	note 4	—	−55	—	dB

Notes

- G_{UM} is the maximum unilateral power gain, assuming S_{12} is zero and $G_{UM} = 10 \log \frac{|S_{21}|^2}{(1 - |S_{11}|^2)(1 - |S_{22}|^2)}$ dB.
- $d_{im} = -60\text{ dB}$ (DIN 45004B); $I_C = 70\text{ mA}$; $V_{CE} = 8\text{ V}$; $R_L = 75\text{ }\Omega$; $T_{amb} = 25\text{ °C}$;
 $V_p = V_o$ at $d_{im} = -60\text{ dB}$;
 $V_q = V_o - 6\text{ dB}$; $f_p = 445.25\text{ MHz}$;
 $V_r = V_o - 6\text{ dB}$; $f_q = 453.25\text{ MHz}$; $f_r = 455.25\text{ MHz}$;
measured at $f_{(p+q-r)} = 443.25\text{ MHz}$.
- $d_{im} = -60\text{ dB}$ (DIN 45004B); $I_C = 70\text{ mA}$; $V_{CE} = 8\text{ V}$; $R_L = 75\text{ }\Omega$; $T_{amb} = 25\text{ °C}$;
 $V_p = V_o$ at $d_{im} = -60\text{ dB}$; $f_p = 795.25\text{ MHz}$;
 $V_q = V_o - 6\text{ dB}$; $f_q = 803.25\text{ MHz}$;
 $V_r = V_o - 6\text{ dB}$; $f_r = 805.25\text{ MHz}$;
measured at $f_{(p+q-r)} = 793.25\text{ MHz}$.
- $I_C = 50\text{ mA}$; $V_{CE} = 8\text{ V}$; $V_o = 50\text{ dBmV}$;
 $f_{(p+q)} = 810\text{ MHz}$; $f_p = 250\text{ MHz}$; $f_q = 560\text{ MHz}$.

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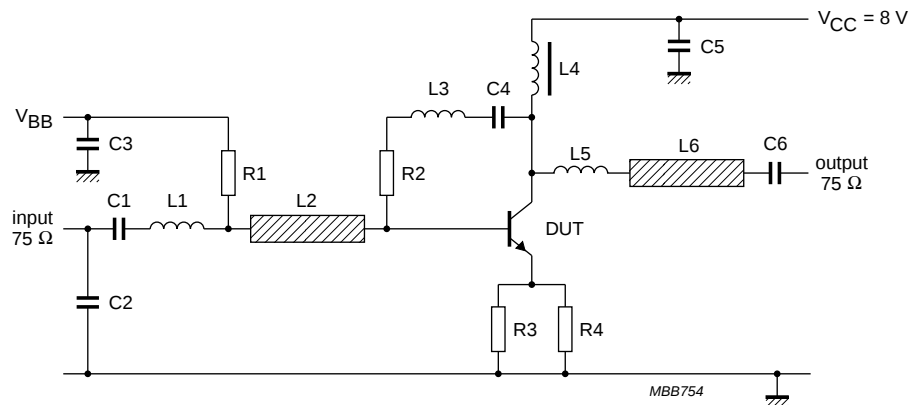


Fig.2 Intermodulation distortion and second order intermodulation distortion test circuit.

List of components (see test circuit)

DESIGNATION	DESCRIPTION	VALUE	UNIT	DIMENSIONS	CATALOGUE NO.
C2	multilayer ceramic capacitor	1.2	pF		2222 851 12128
C1, C4, C6, C7	multilayer ceramic capacitor	10	nF		2222 590 08627
C3	multilayer ceramic capacitor	10	nF		2222 851 12128
C5 (note 1)	multilayer ceramic capacitor	10	nF		2222 629 08103
C8	multilayer ceramic capacitor	1.5	pF		2222 851 12158
L1 (note 1)	1.5 turns 0.4 mm copper wire			int. dia. 3 mm; winding pitch 1 mm	
L2	microstripline	75	Ω	length 22 mm; width 2.5 mm	
L3 (note 1)	0.4 mm copper wire	≈ 24	nH	length 30 mm	
L4 (note 1)	0.4 mm copper wire	≈ 3.6	nH	length 4 mm	
L5	microstripline	75	Ω	length 19 mm; width 2.5 mm	
L6	Ferroxcube choke	5	μ H		3122 108 20153
R1	metal film resistor	10	Ω		2322 180 73103
R2 (note 1)	metal film resistor	220	Ω		2322 180 73221
R3, R4	metal film resistor	30	Ω		2322 180 73309

Note

- Components C5, L1, L3, L4, and R2 are mounted on the underside of the PCB.
The circuit is constructed on a double copper-clad printed circuit board with PTFE dielectric ($\epsilon_r = 2.2$); thickness $\frac{1}{16}$ inch; thickness of copper sheet $2 \times 35 \mu\text{m}$; see Fig.2.

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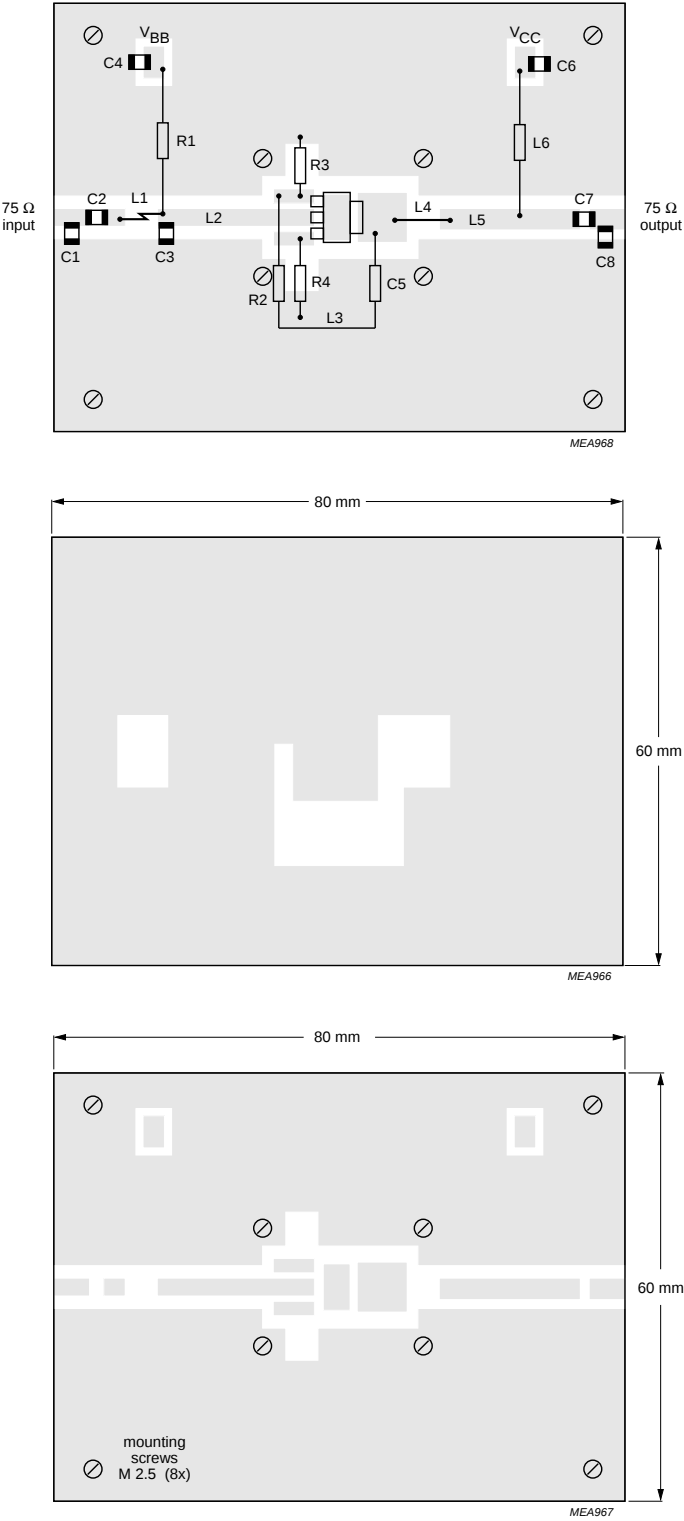
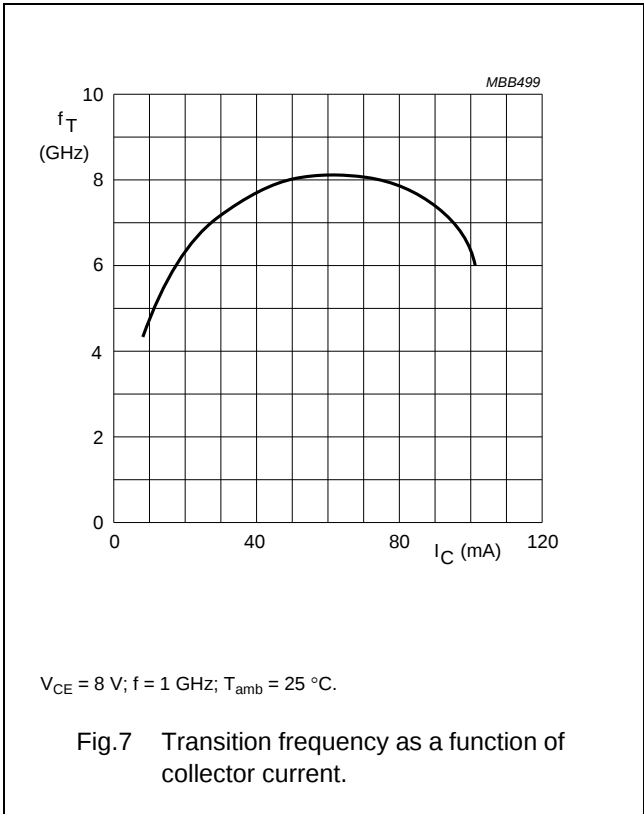
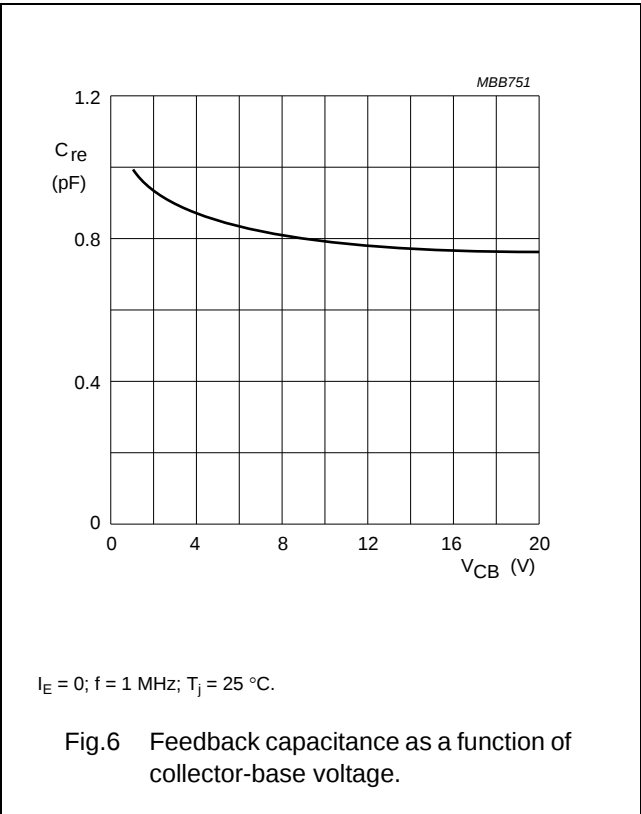
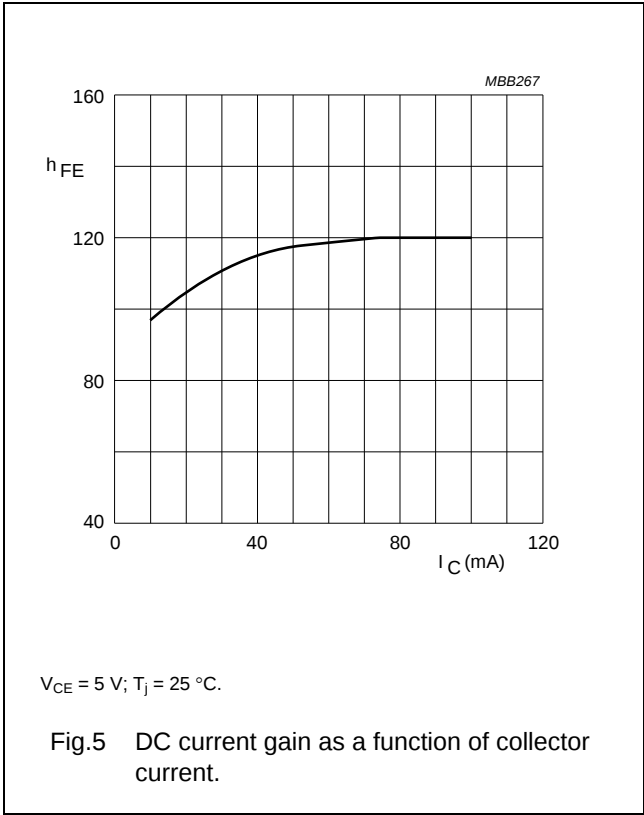
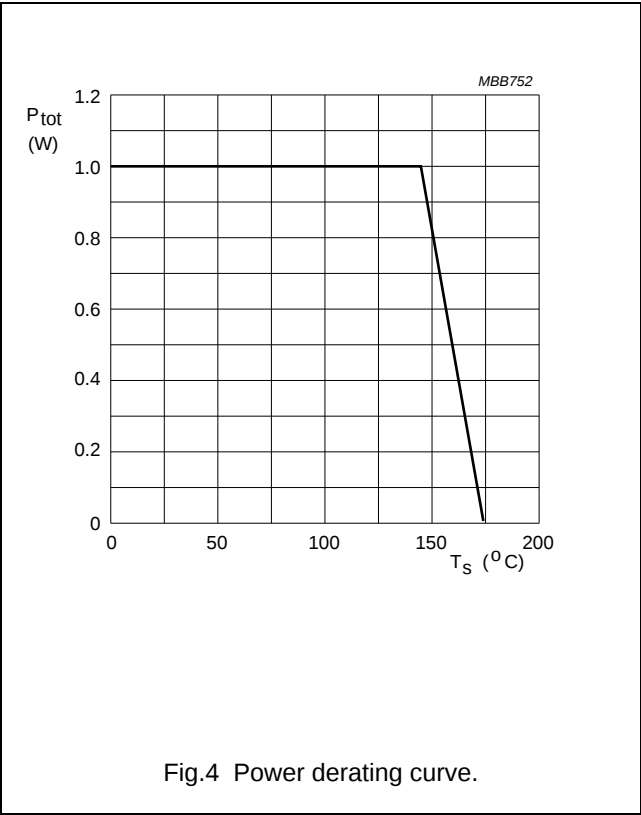


Fig.3 Intermodulation distortion and second order intermodulation distortion printed-circuit board.

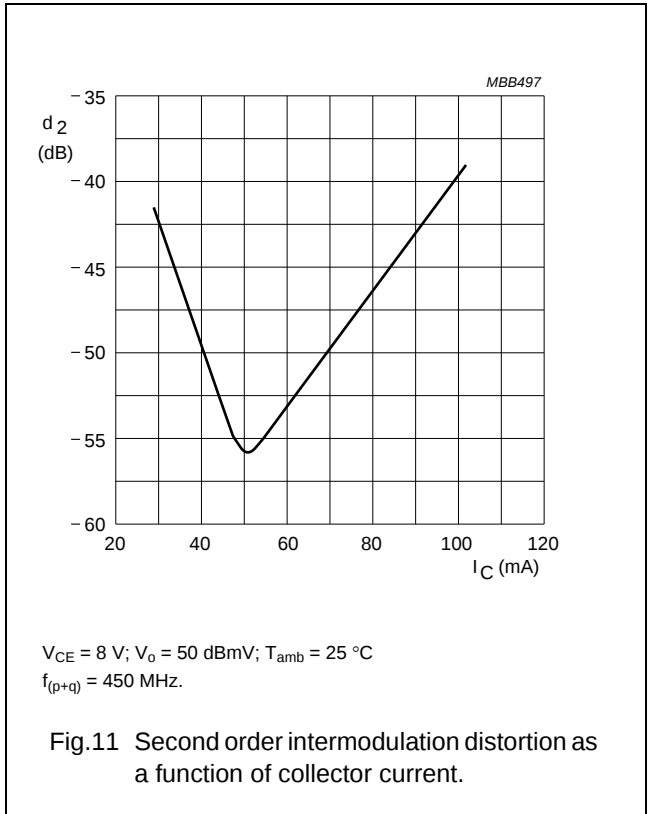
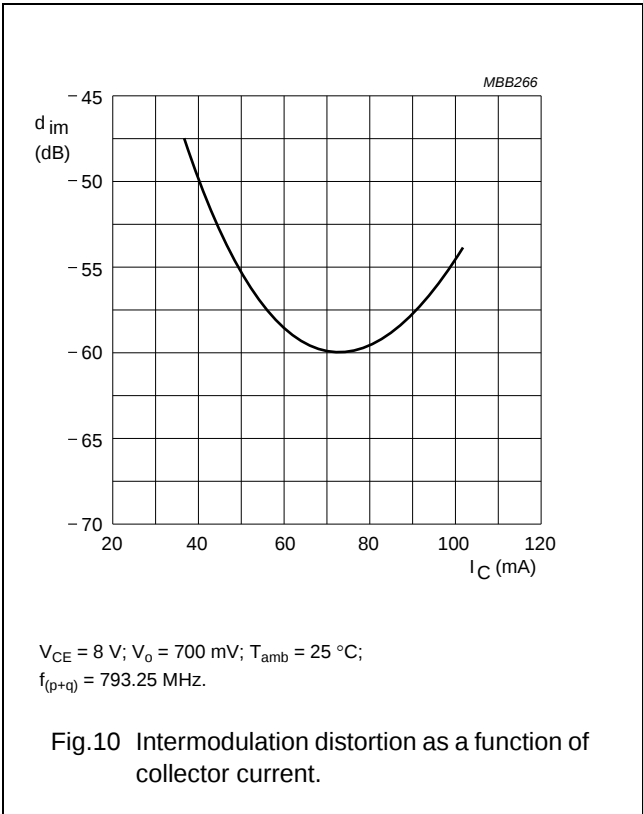
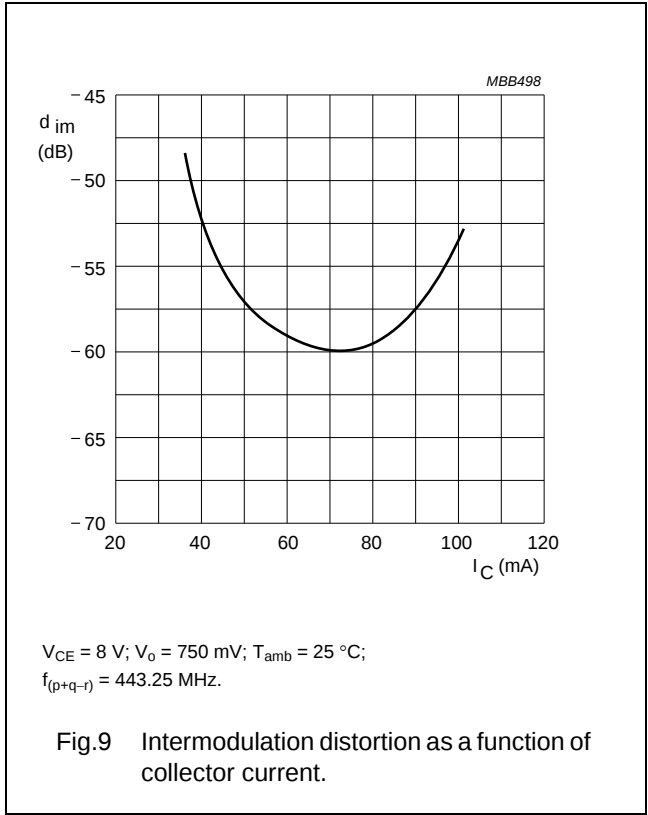
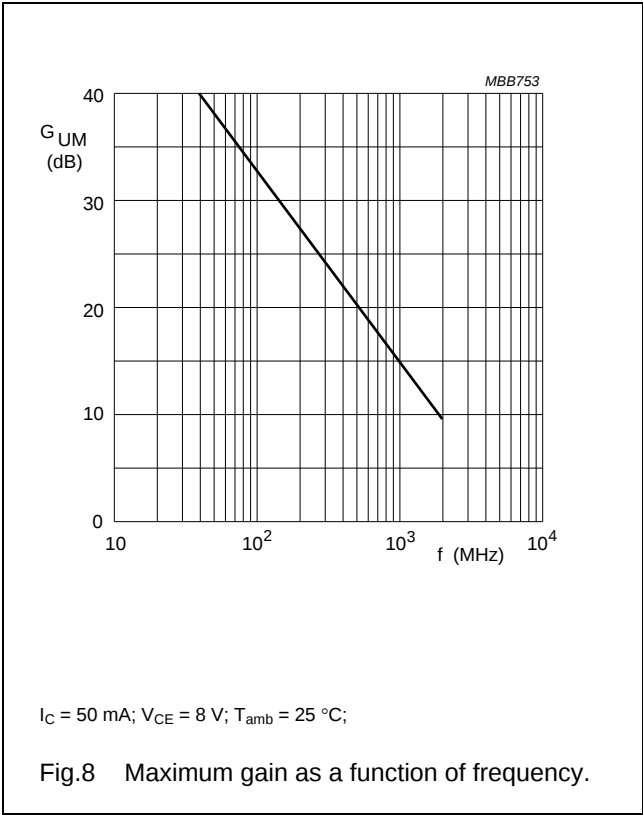
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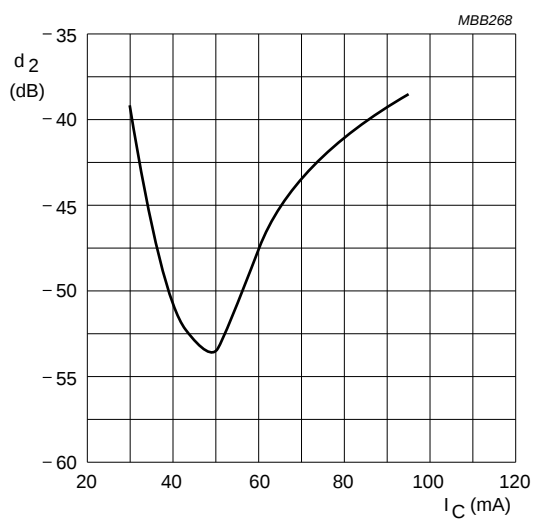
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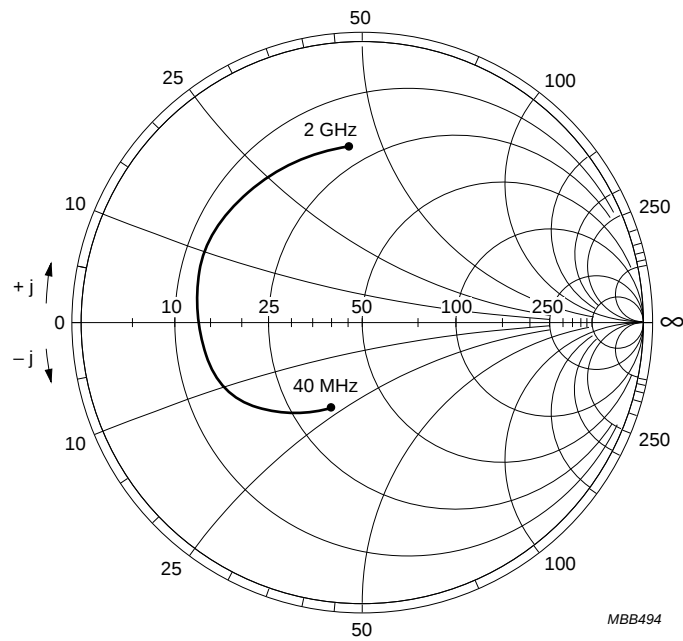
$V_{CE} = 8 \text{ V}$; $V_0 = 50 \text{ dBmV}$; $T_{amb} = 25 \text{ }^\circ\text{C}$

$f_{(p+q)} = 810 \text{ MHz}$.

Fig.12 Second order intermodulation distortion as a function of collector current.

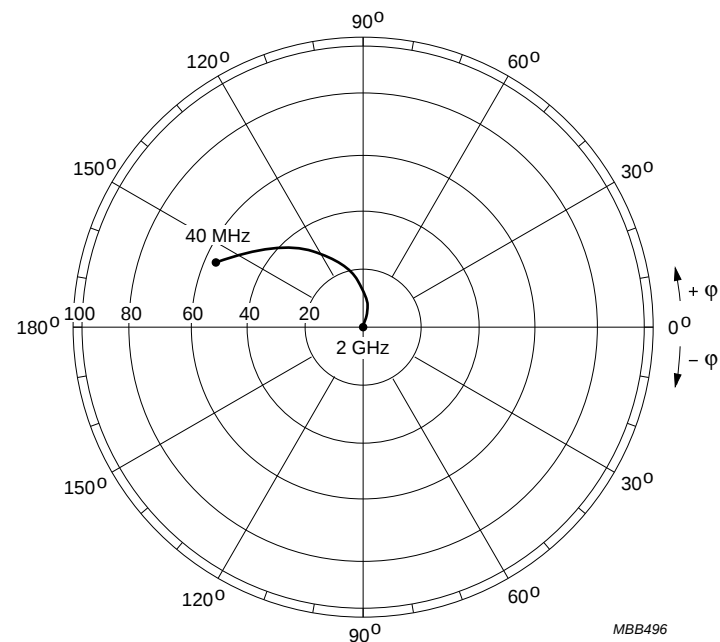
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$I_C = 50\text{ mA}$; $V_{CE} = 8\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; $Z_0 = 50\text{ }\Omega$.

Fig.13 Common emitter input reflection coefficient (S_{11}).

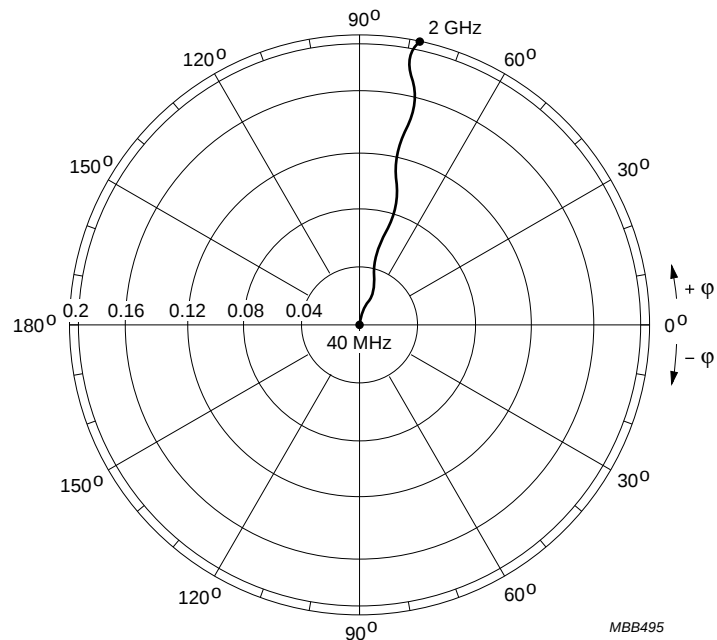


$I_C = 50\text{ mA}$; $V_{CE} = 8\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.14 Common emitter forward transmission coefficient (S_{21}).

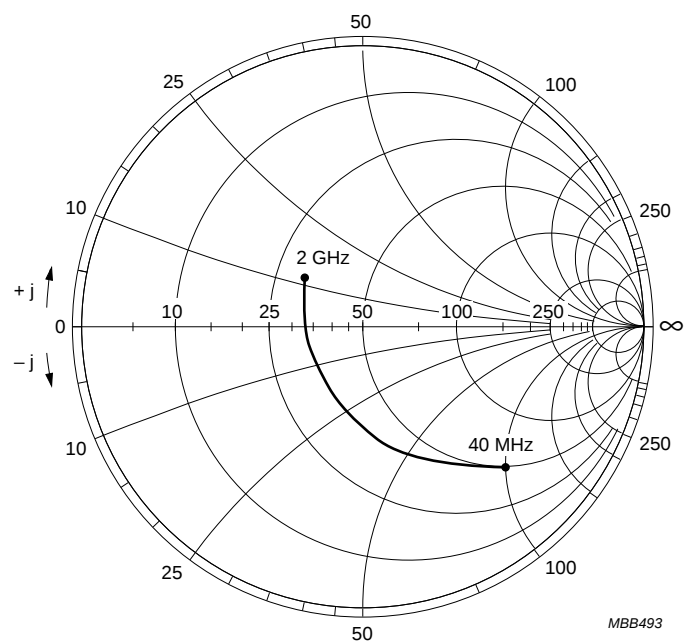
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$I_C = 50\text{ mA}$; $V_{CE} = 8\text{ V}$; $T_{amb} = 25\text{ °C}$.

Fig.15 Common emitter reverse transmission coefficient (S_{12}).



$I_C = 50\text{ mA}$; $V_{CE} = 8\text{ V}$; $T_{amb} = 25\text{ °C}$; $Z_0 = 50\text{ }\Omega$.

Fig.16 Common emitter output reflection coefficient (S_{22}).

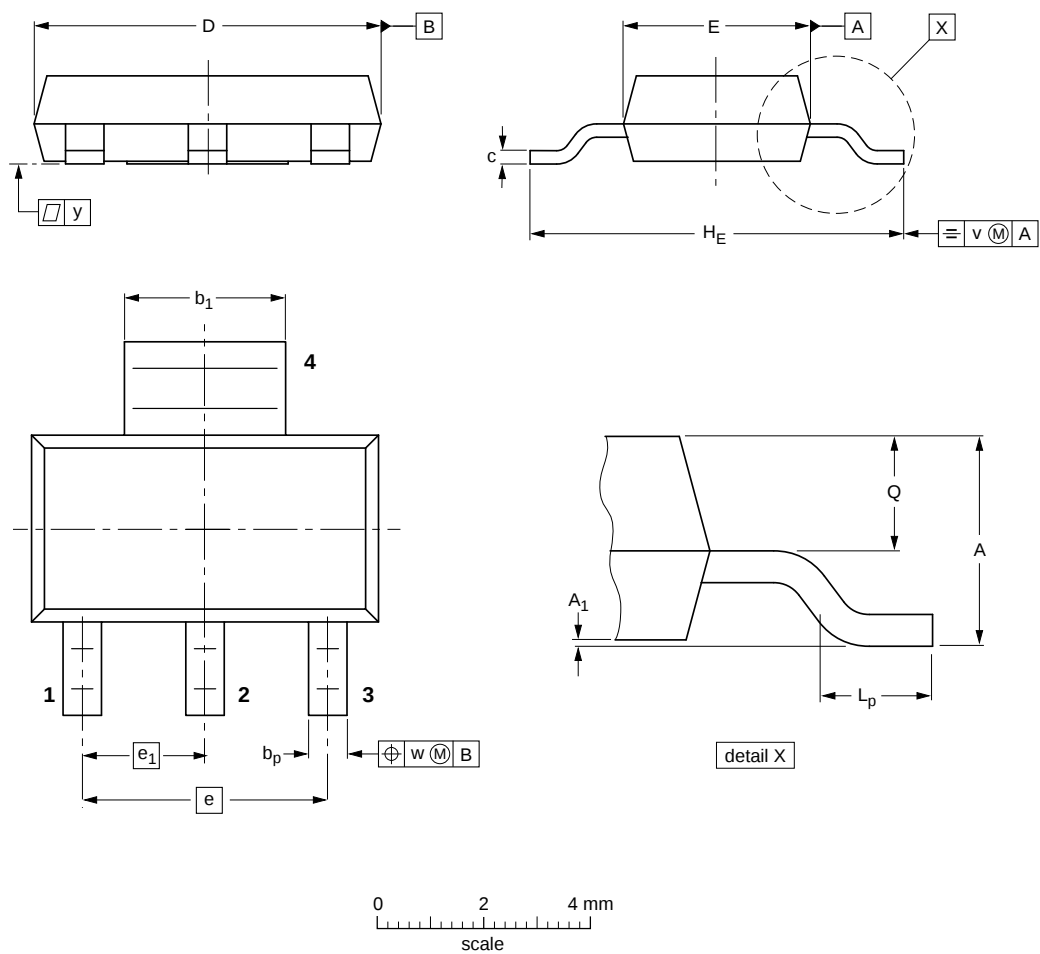
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PACKAGE OUTLINE

Plastic surface-mounted package with increased heatsink; 4 leads

SOT223



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b _p	b ₁	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT223			SC-73			04-11-10 06-03-16

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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